Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons
Kozlovski, Vitali V.; **Korolkov, Oleg**; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 https://doi.org/10.4028/www.scientific.net/MSF.1004.231 Conference Proceedings at Scopus Article at Scopus

Dependence of the carrier removal rate in 4H-SIC PN structures on irradiation temperature
Lebedev, Alexander A.; Davydovskaya, Klavdya S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 730-733 https://doi.org/10.4028/www.scientific.net/MSF.963.730 Conference proceeding at Scopus Article at Scopus

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes
Kozlovski, Vitali V.; **Korolkov, Oleg**; Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshteĭn, Michael E.; **Sleptšuk, Natalja**; Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 https://doi.org/10.1134/S1063785020030244 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS